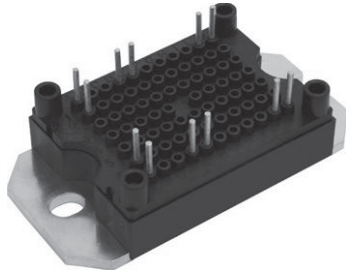


HEXFRED® Ultrafast Diodes, 30 A (Single Phase Bridge MTP Power Modules)



MTP

FEATURES

- Low profile package
- Low t_{rr} and Q_{rr}
- Soft reverse recovery
- Direct mounting to heatsink
- Round pin with PCB solderable terminals
- UL approved file E78996
- Low junction to case thermal resistance
- 3500 V_{RMS} insulation voltage
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRIMARY CHARACTERISTICS	
V_R	1200 V
V_F (typical) at $I_F = 30$ A	2.46 V
I_O at 88 °C	30 A
Q_{rr} (typical)	720 nC
I_{RRM} (typical)	12 A
t_{rr} (typical)	121 ns
$di_{(rec)M}/dt$ (typical)	300 A/ μ s
Package	MTP
Circuit configuration	Single phase bridge

DESCRIPTION

A range of extremely compact single-phase rectifier bridges offering efficient and reliable operation.

The low profile package has been specifically conceived to maximize space saving and optimize the electrical layout of the application specific power supplies.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		1200	V
Continuous forward current per diode	I_F	$T_C = 88$ °C	30	A
Single pulse forward current per diode	I_{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25$ °C	300	
Maximum repetitive forward current per diode	I_{FRM}		200	
Maximum power dissipation per diode	P_D	$T_C = 88$ °C	85	W
Operating junction temperature range	T_J		-40 to +150	°C

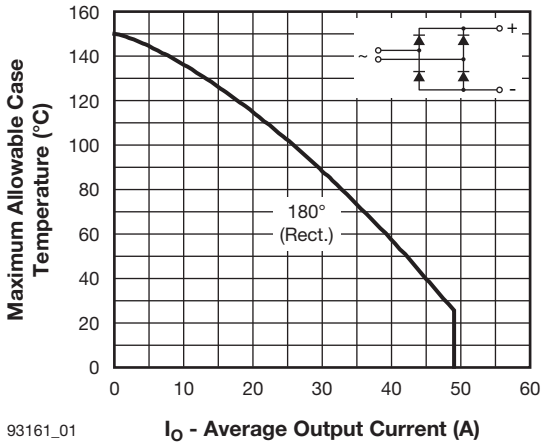
ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100$ μ A	1200	-	-	V
Forward voltage	V_F	$I_F = 30$ A	-	2.46	3.34	V
		$I_F = 60$ A	-	3.11	4.45	
		$I_F = 30$ A, $T_J = 125$ °C	-	2.32	2.96	
		$I_F = 60$ A, $T_J = 125$ °C	-	3.07	3.96	
Reverse leakage current	I_R	$V_R = 1200$ V	-	2.8	50	μ A
		$V_R = 1200$ V, $T_J = 125$ °C	-	2	10	mA
Junction capacitance	C_T	$V_R = 200$ V	-	50	75	pF



DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$	$I_F = 30\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	-	121	170	ns
		$T_J = 125\text{ }^\circ\text{C}$		-	180	260	
Peak recovery current	I_{RR}	$T_J = 25\text{ }^\circ\text{C}$		-	12	16	A
		$T_J = 125\text{ }^\circ\text{C}$		-	17	24	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$		-	720	1350	nC
		$T_J = 125\text{ }^\circ\text{C}$		-	1540	2310	
Peak rate of fall of recovery current during t_b	$dl_{(rec)M}/dt$	$T_J = 25\text{ }^\circ\text{C}$		-	300	-	$\text{A}/\mu\text{s}$
		$T_J = 125\text{ }^\circ\text{C}$		-	265	-	

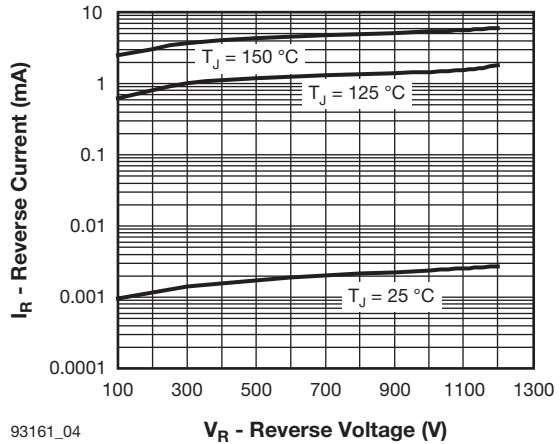
INSULATION TABLE				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
RMS insulation voltage	V_{INS}	$T_J = 25\text{ }^\circ\text{C}$, all terminals shorted, $f = 50\text{ Hz}$, $t = 1\text{ s}$	3500	V

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +150	$^\circ\text{C}$
Maximum thermal resistance, per module junction to case per junction	R_{thJC}	DC operation	0.18	$^\circ\text{C}/\text{W}$
			0.73	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.06	
Approximate weight			65	g
Mounting torque, $\pm 10\%$ to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.	4	Nm



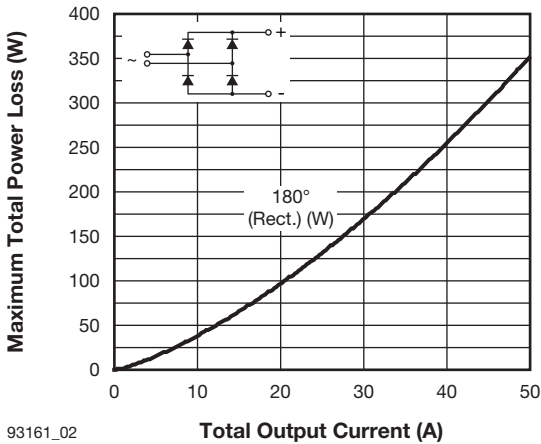
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Fig. 1 - Output Current Ratings Characteristics



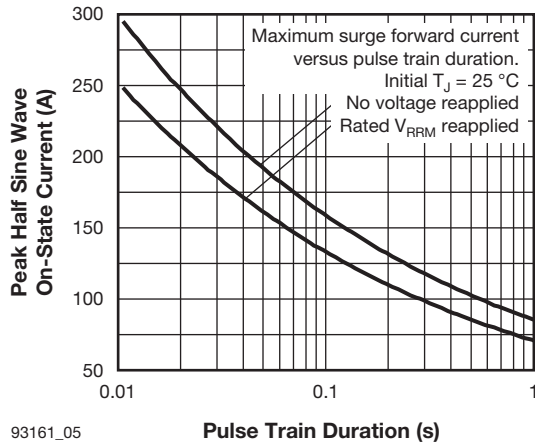
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Fig. 4 - Typical Values of Reverse Current vs. Reverse Voltage (Per Diode)



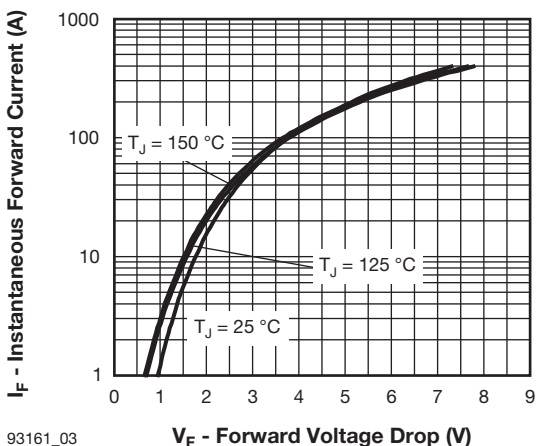
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Fig. 2 - On-State Power Loss Characteristics



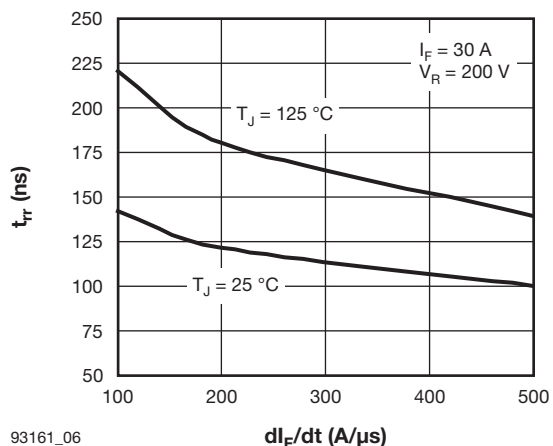
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Fig. 5 - Maximum Surge Forward Current (Per Diode)



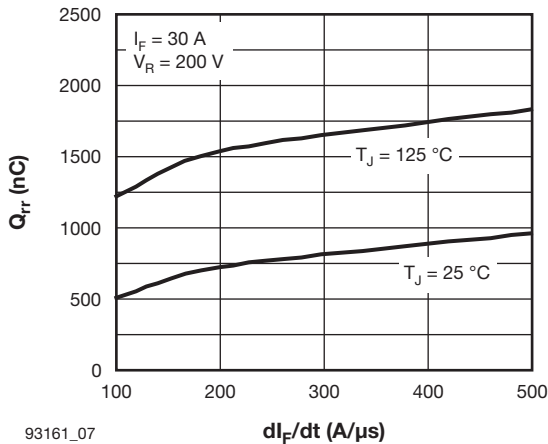
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Fig. 3 - Typical Forward Voltage Drop Characteristics (Per Diode)



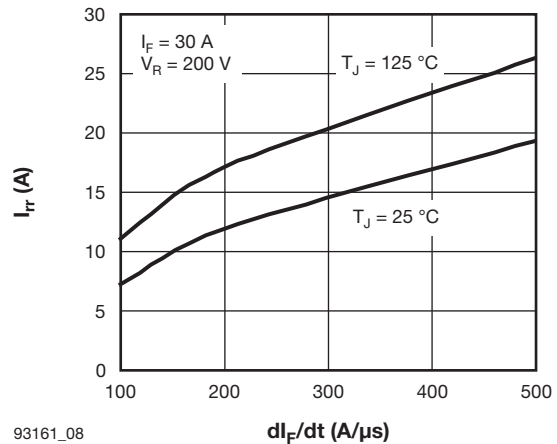
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Fig. 6 - Typical Reverse Time vs. di_F/dt (Per Diode)



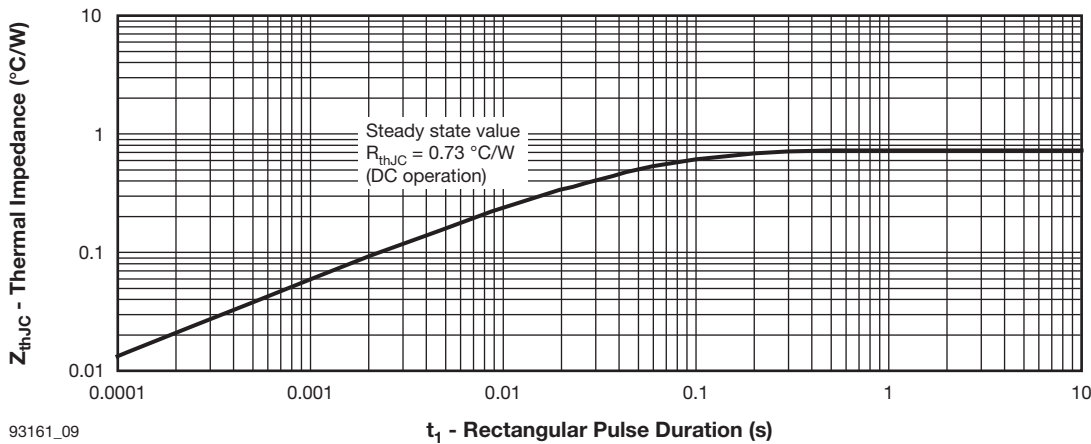
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Fig. 7 - Typical Stored Charge vs. di/dt (Per Diode)



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Fig. 8 - Typical Recovery Current vs. di/dt (Per Diode)



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Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Diode)

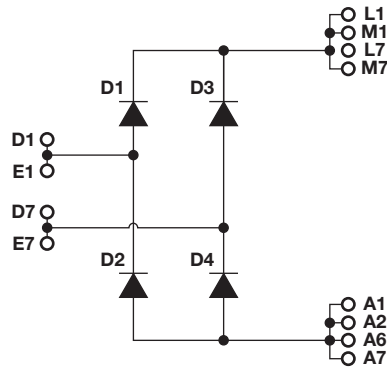
ORDERING INFORMATION TABLE

Device code	VS-	3	5	MT	120	P	B
	①	②	③	④	⑤		⑥

- 1** - Vishay Semiconductors product
- 2** - Current rating (3 = 30 A)
- 3** - Circuit configuration code: 5 = single phase bridge
- 4** - Package indicator: MT = MTP
- 5** - Voltage code: code x 10 (120 = 1200 V)
- 6** - Pinout code: B = round pins



CIRCUIT CONFIGURATION



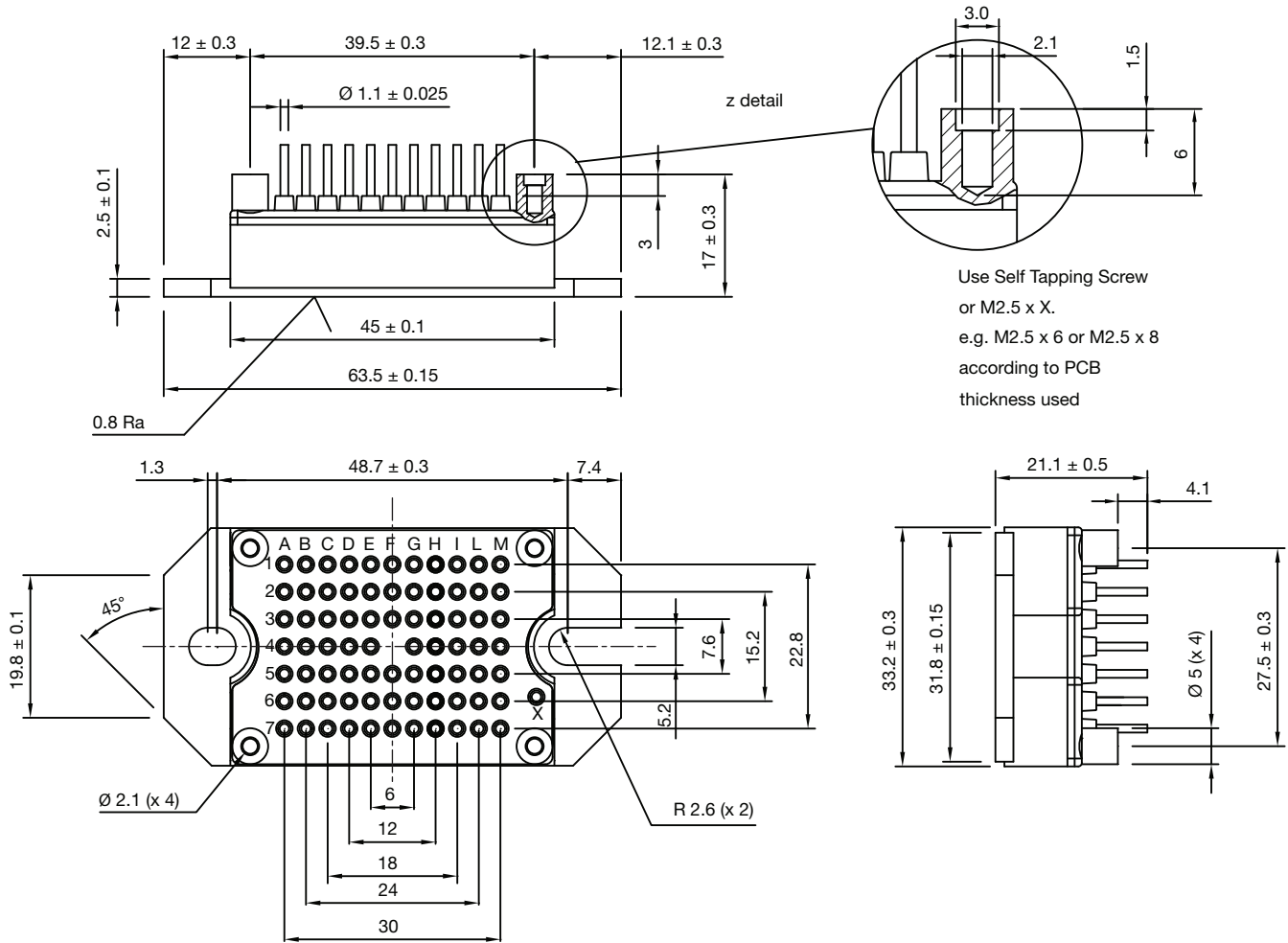
LINKS TO RELATED DOCUMENTS

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95383



MTP - Full Pin

DIMENSIONS in millimeters



Use Self Tapping Screw
or M2.5 x X.
e.g. M2.5 x 6 or M2.5 x 8
according to PCB
thickness used

PINS POSITION
WITH TOLERANCE $\text{Ø } 0.6$



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